

EXHIBIT F

First Japanese Priority Application

Claim 2 of the '925 Patent

A light emitting device, comprising

- a) a light emitting component and
- b) a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light;
- c) wherein said light emitting component comprises a nitride compound semiconductor represented by the formula: $In_iGa_jAl_kN$ where $0 \leq i, 0 \leq j, 0 \leq k$ and $i+j+k=1$ and
- d) wherein the phosphor used contains an yttrium-aluminum-garnet fluorescent

the LED chip is a nitride compound semiconductor. The photoluminescent fluorescent substance is an yttrium-aluminum-garnet fluorescent substance activated with cerium.

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fluorescent substances activated with cerium. The LED chip is the light emitting element is made by forming a light emitting layer of semiconductor such as InGaN on a substrate in a process. The semiconductor structure may be homo-

in order to form gallium nitride of good crystalinity. A layer of GaN, AlN, etc. is formed on the sapphire substrate.

Fourth Japanese Priority Appl

Claim 2 of the '925 Patent

A light emitting device, comprising

- a) a light emitting component and
- b) a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light;
- c) **wherein said light emitting component comprises a nitride compound semiconductor represented by the formula: $In_iGa_jAl_kN$ where $0 \leq i, 0 \leq j, 0 \leq k$ and $i+j+k=1$ and**
- d) wherein the phosphor used contains an yttrium-aluminum-garnet fluorescent

the LED chip is a nitride compound semiconductor. The photoluminescent fluorescent substance is an yttrium-aluminum-garnet fluorescent substance activated with cerium.

fluorescent substances activated with cerium. The LED is the light emitting element is made by forming a light emitting layer of semiconductor such as InGaN on a substrate in a growth process. The semiconductor structure may be homo-

in order to form gallium nitride of good crystalinity. A layer of GaN, AlN, etc. is formed on the sapphire substrate.

Fifth Japanese Priority Application

Claim 2 of the '925 Patent

A light emitting device, comprising

- a) a light emitting component and
- b) a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light;
- c) **wherein said light emitting component comprises a nitride compound semiconductor represented by the formula: $In_iGa_jAl_kN$ where $0 \leq i, 0 \leq j, 0 \leq k$ and $i+j+k=1$ and**
- d) wherein the phosphor used contains an yttrium-aluminum-garnet fluorescent

As one embodiment of the light emitting device type LED is shown in Fig. 1. A LED chip 102 employing nitrate semiconductor is fixed in the casing of the LED by means of epoxy resin or the like. The LED chip 102 **a light emitting component having a $In_{0.4}Ga_{0.6}N$ semiconductor light emitting layer with a thickness of 470 nm.**

compositions may be used. **The LED chip** which is a light emitting component can be made by forming light emitting layer of **semiconductor such as AlN, InN, GaN, InGaN or InN** on a substrate in the MOCVD process. The semiconductor s